Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002-1) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Thermally efficient package in a small form factor (3.3 mm x 3.3 mm footprint)

3. Applications

- Power Management
- High-speed line driver
- · High-side load switch
- Relay driver

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = -10 V; T _{mb} = 25 °C		-	-	-20	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C		-	-	46	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = -10 \text{ V}; I_D = -3.7 \text{ A}; T_j = 25 \text{ °C}$		-	51	62	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source	رف ف ف	D
3	S	source		
4	G	gate		$_{G}$ \downarrow \downarrow \downarrow
5	D	drain		
6	D	drain	Laaal Laaal	S
7	D	drain	8 7 6 5 MI DAK 22 (SOT 2002 4)	017aaa094
8	D	drain	MLPAK33 (SOT8002-1)	

6. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
PXP062-60QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1					

7. Marking

Table 4. Marking codes

Type number	Marking code
PXP062-60QL	NXH

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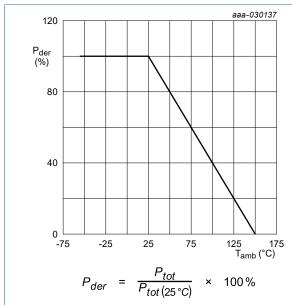
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{mb} = 25 °C		-	-20	Α
		V _{GS} = -10 V; T _{mb} = 100 °C		-	-13	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-80	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C		-	46	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain d	iode					
Is	source current	T _{mb} = 25 °C		-	-20	Α
I _{SM}	peak source current	T_{mb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-80	Α
Avalanche rug	gedness			'	'	'
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$V_{sup} \le -60 \text{ V}; V_{GS} = -10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega; I_D = -19.5 \text{ A}; unclamped$	[1] [2]	-	36	mJ
I _{AS}	non-repetitive avalanche current	$T_{j(init)} = 25 ^{\circ}C$	[3]	-	-19.5	А

- Single-pulse avalanche rating limited by maximum junction temperature. Refer to application note AN10273 for further information.
- [2]
- Protected by 100% test.



Normalized total power dissipation as a Fig. 1. function of ambient temperature

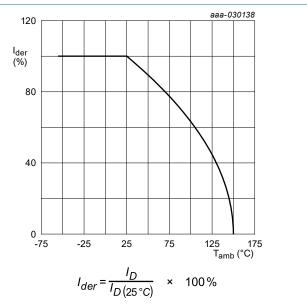


Fig. 2. Normalized continuous drain current as a function of ambient temperature

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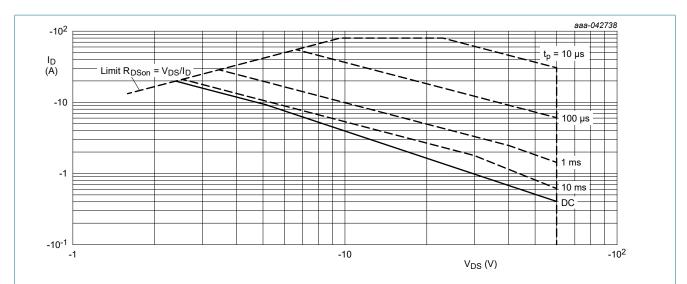


Fig. 3. Safe operating area; junction to mounting base; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	60	80	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	1.8	2.7	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

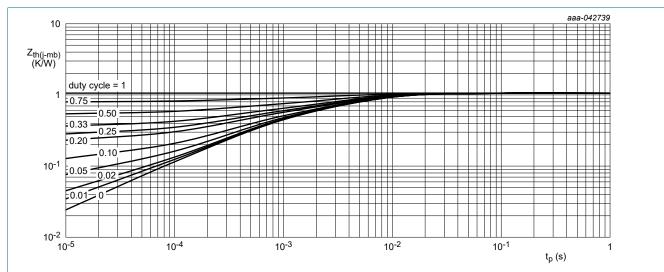


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1.4	-2	-2.7	V
I _{DSS}	drain leakage current	$V_{DS} = -60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -3.7 A; T_j = 25 °C	-	51	62	mΩ
	resistance	V_{GS} = -10 V; I_D = -3.7 A; T_j = 150 °C	-	99	120	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -3.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	65	80	mΩ
9fs	forward transconductance	V _{DS} = -5 V; I _D = -3.7 A; T _j = 25 °C	-	12.7	-	S
R_G	gate resistance	f = 1 MHz	-	12	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -30 \text{ V}; I_D = -3.7 \text{ A}; V_{GS} = -10 \text{ V};$	-	19	28	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	3.5	-	nC
Q_{GD}	gate-drain charge	1	-	4.1	-	nC
C _{iss}	input capacitance	V _{DS} = -30 V; f = 1 MHz; V _{GS} = 0 V;	-	1070	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	99	-	pF
C _{rss}	reverse transfer capacitance		-	48	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -30 \text{ V}; I_D = -3.7 \text{ A}; V_{GS} = -10 \text{ V};$	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	5	-	ns
t _{d(off)}	turn-off delay time	1	-	37	-	ns
t _f	fall time	1	-	179	-	ns
Source-drai	in diode		I .		<u> </u>	
V_{SD}	source-drain voltage	$I_S = -1.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.7	-1.2	V
t _{rr}	reverse recovery time	$I_S = -1.6 \text{ A}; dI_S/dt = 100 \text{ A/µs};$	-	21	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = -30 \text{ V}; T_j = 25 ^{\circ}\text{C}$	_	17	_	nC

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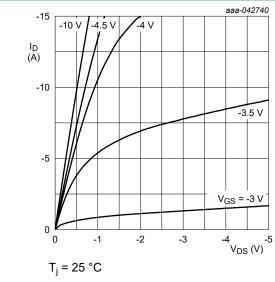


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

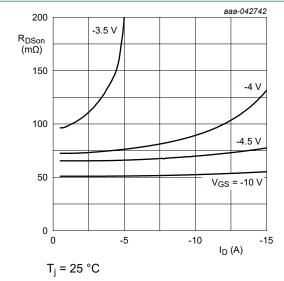


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values

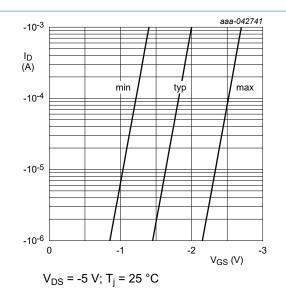


Fig. 6. Sub-threshold drain current as a function of gate-source voltage

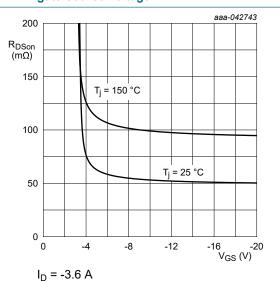


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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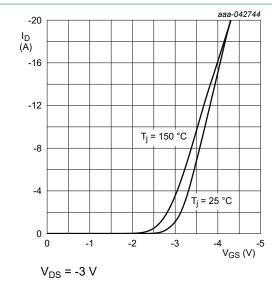


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

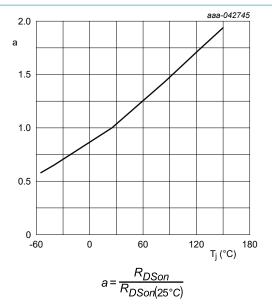


Fig. 10. Normalized drain-source on-state resistance as a function of junction temperature; typical values

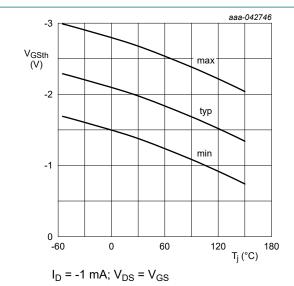
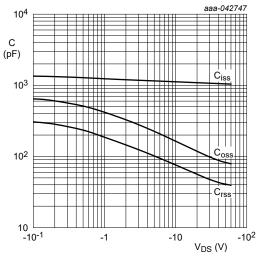


Fig. 11. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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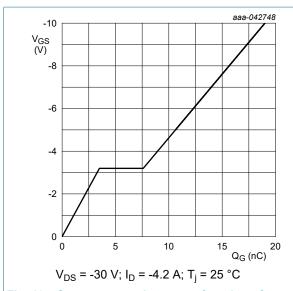


Fig. 13. Gate-source voltage as a function of gate charge; typical values

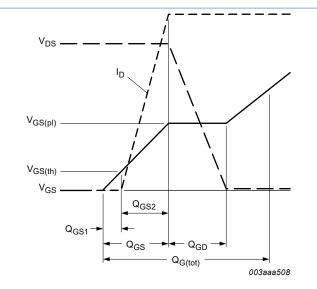


Fig. 14. Gate charge waveform definitions

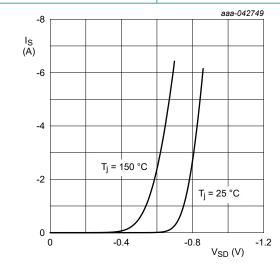
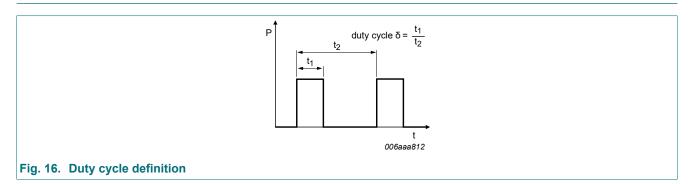


Fig. 15. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

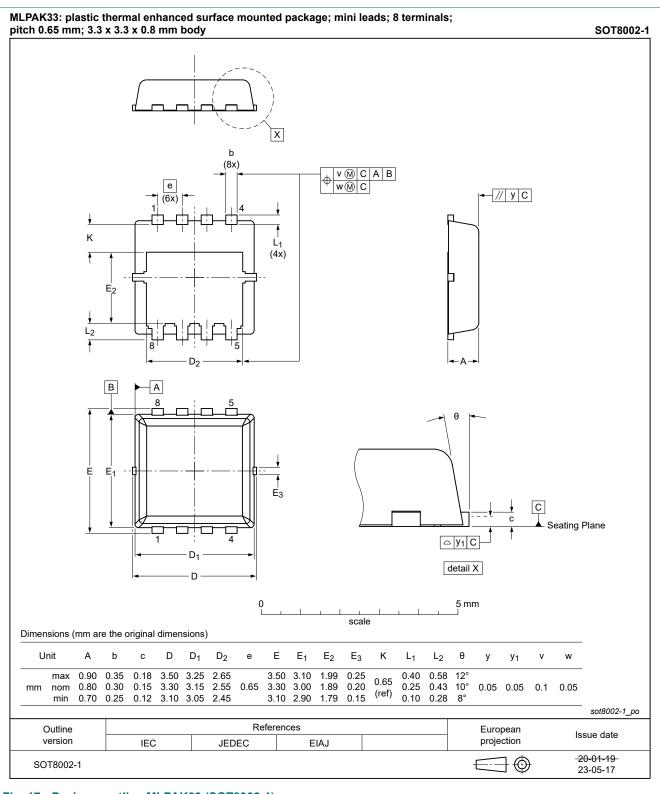
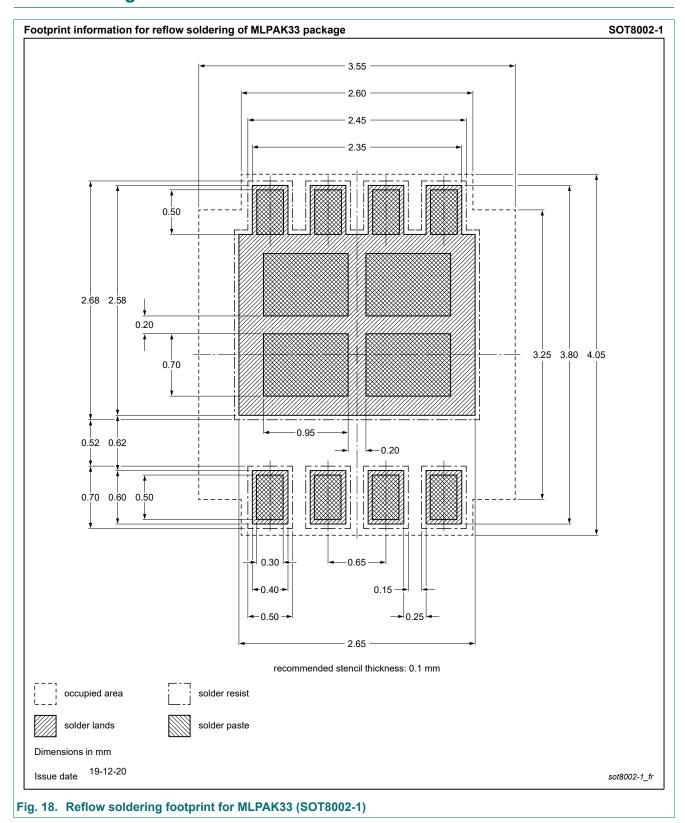


Fig. 17. Package outline MLPAK33 (SOT8002-1)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PXP062-60QL v.1	20250520	Product data sheet	-	-

60 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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